



## IN THE UNITED STATES PATENT AND TRANDMARK OFFICE

Patent Application Serial No. .... 10/041,896  
 Filing Date ..... January 7, 2002  
 Inventor ..... Brenda D. Kraus  
 Assignee ..... Micron Technology, Inc.  
 Group Art Unit ..... 2813  
 Examiner ..... Yennhu B. Huynh  
 Attorney Docket No. .... MI22-1859  
 Title: DRAM Circuitry Having Storage Capacitors Which Include Capacitor  
 Dielectric Regions Comprising Aluminum Nitride

#11/Supple  
 IDS  
 Attached  
 1/24/03

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with  
 37 CFR §1.56. Copies of the cited art are included. No admission is made  
 regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 12-30-02By: 

Mark S. Matkin  
 Reg. No. 32,268

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